

The reducing atmosphere of the Spark Plasma Sintering: a disadvantage or an advantage for oxides?

▪

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Summary

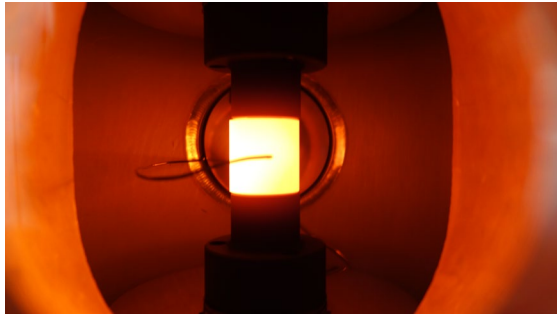
1- Piezoelectric material : $\text{K}_{0.5}\text{Na}_{0.5}\text{NbO}_3$ (KNN)

2- Thermoelectric oxide : $\text{Sr}_{0.95}\text{La}_{0.05}\text{TiO}_3$.

3- Thermoelectric oxide : $\text{La}_{0.66}\text{Ti}_{0.95}\text{Al}_{0.05}\text{O}_3$

4- Ionic conductor: $\text{La}_2\text{Mo}_2\text{O}_9$

Spark plasma sintering – a way for high relative densities



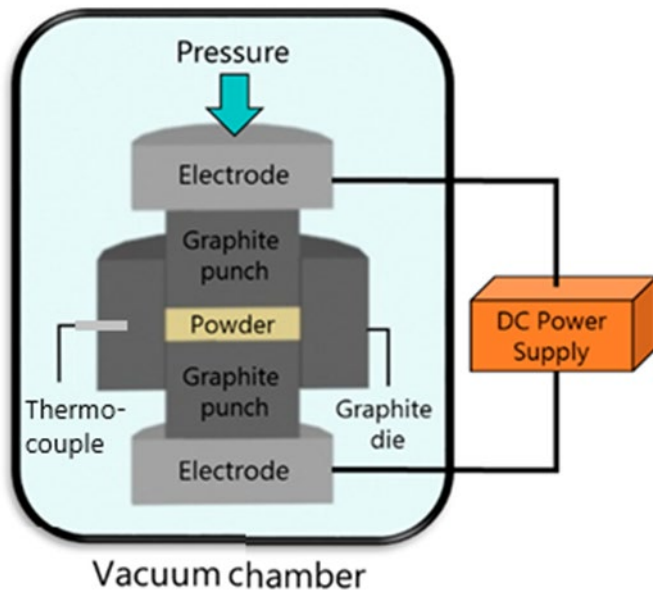
SPS 632Lx –Fuji Electronics
3000 A – 60 kN

Benefits:

- Lower temperature – shorter time
- Prevent alkali volatilization
- High relative densities

Drawbacks ?

- C contamination with graphite materials ?
- Reductive conditions / oxygen losses ?
- Densification mechanisms: creep/ defects ?

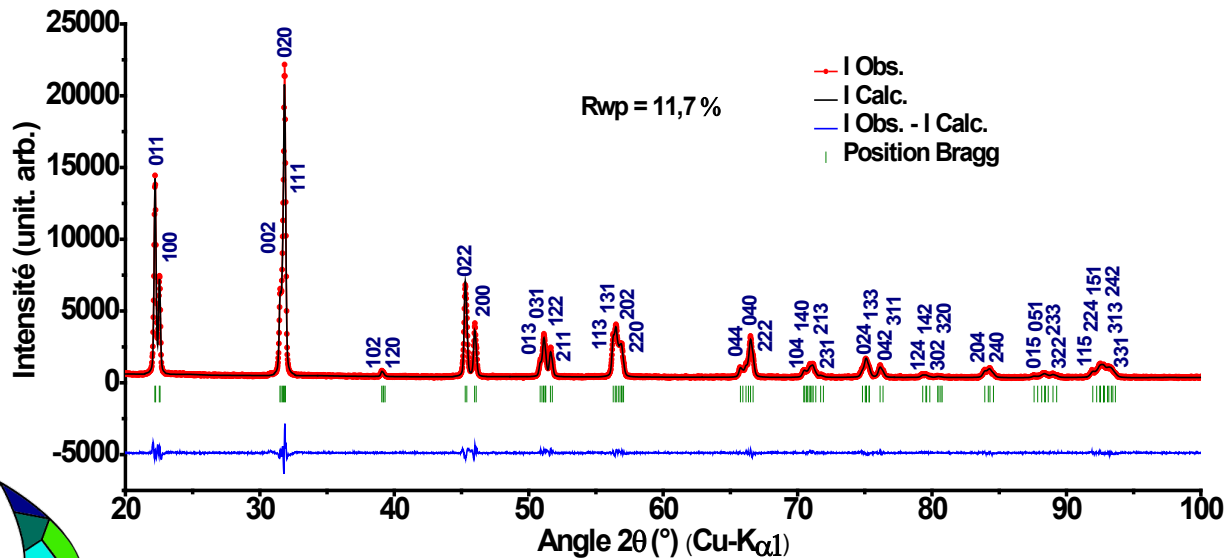
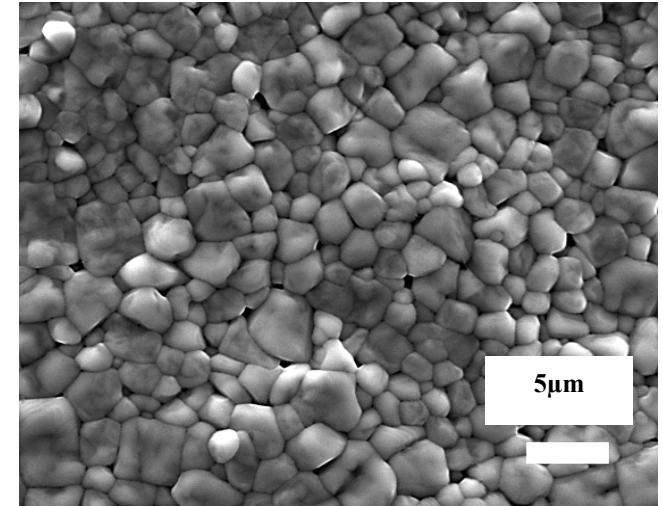
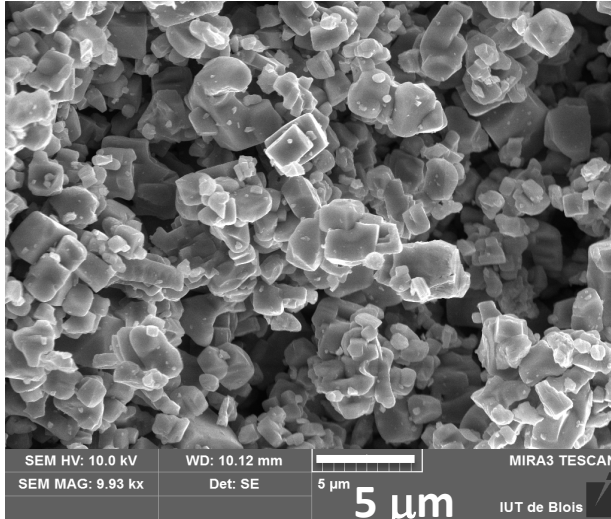


Impact of SPS on piezoelectric material :

$\text{K}_{0.5}\text{Na}_{0.5}\text{NbO}_3$ (KNN)

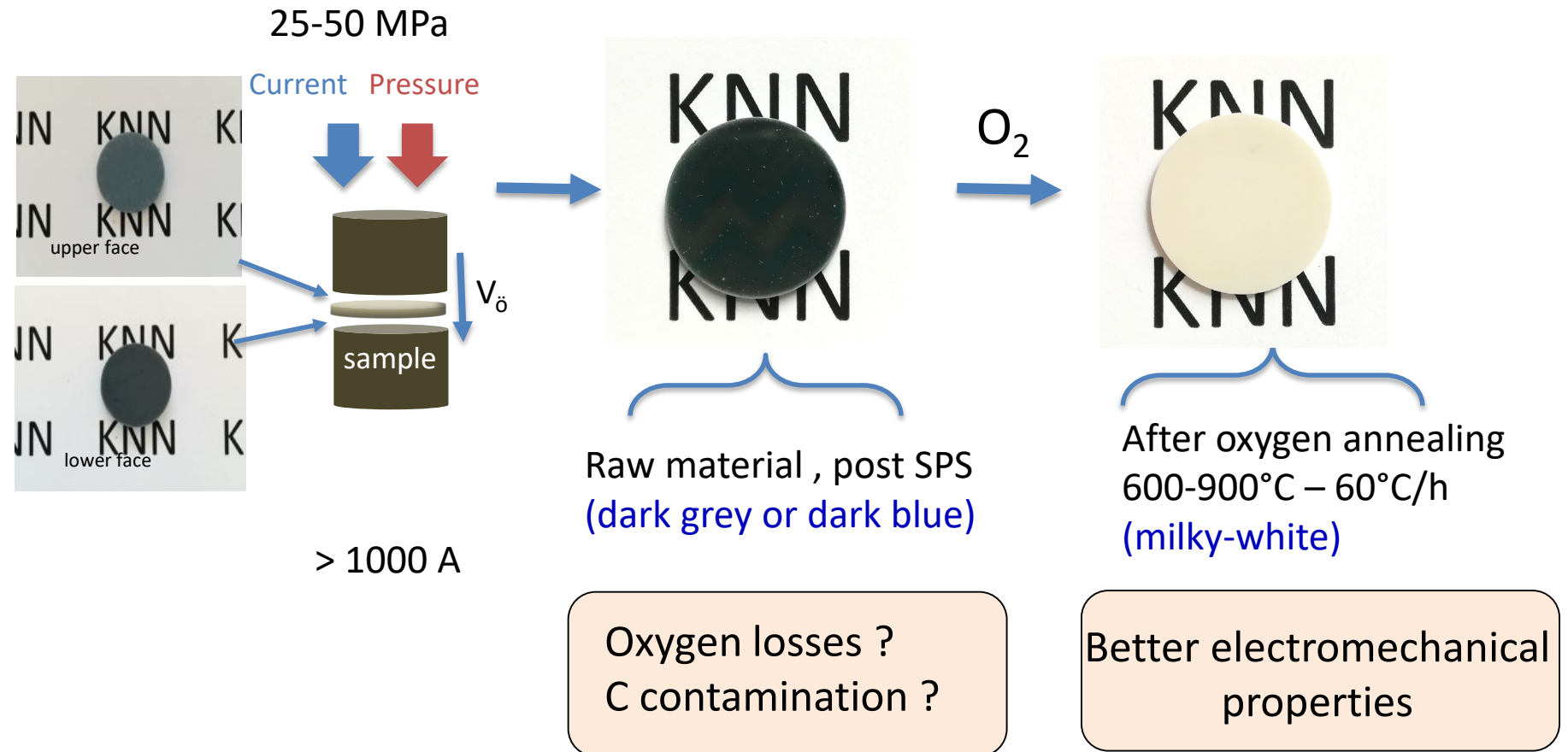
KNN, $K_{0.5}Na_{0.5}NbO_3$

SPS - 920°C - 98% - 3 μ m



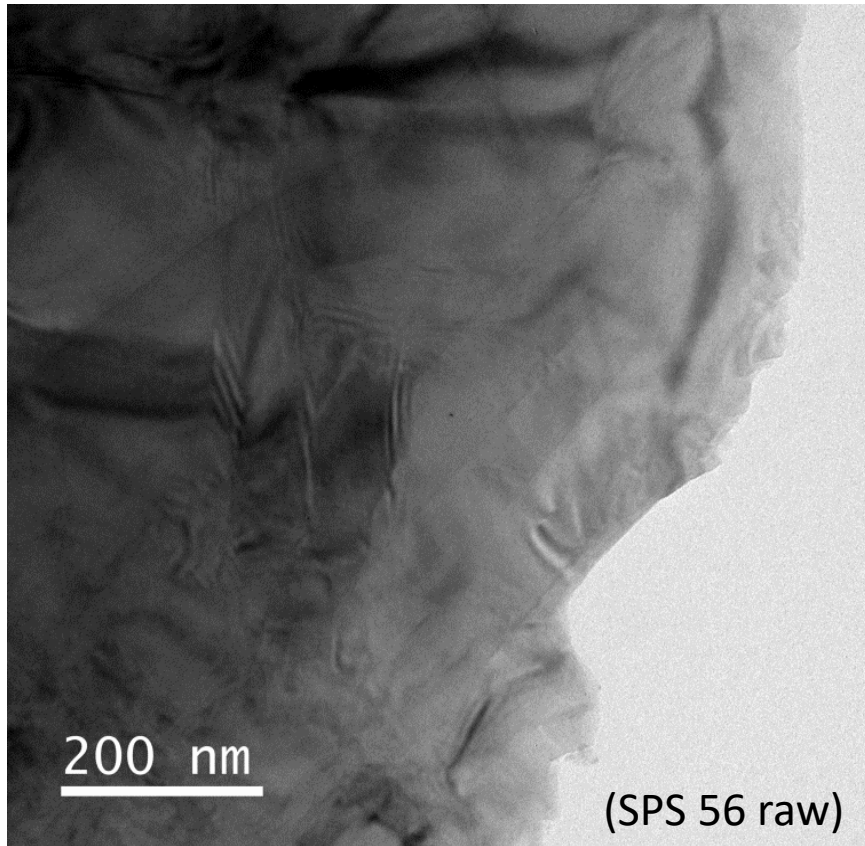
Orthorhombic, $Amm2$
 $a = 3.945 \text{ \AA}$
 $b = 5.646 \text{ \AA}$
 $c = 5.678 \text{ \AA}$

What about drawbacks ?



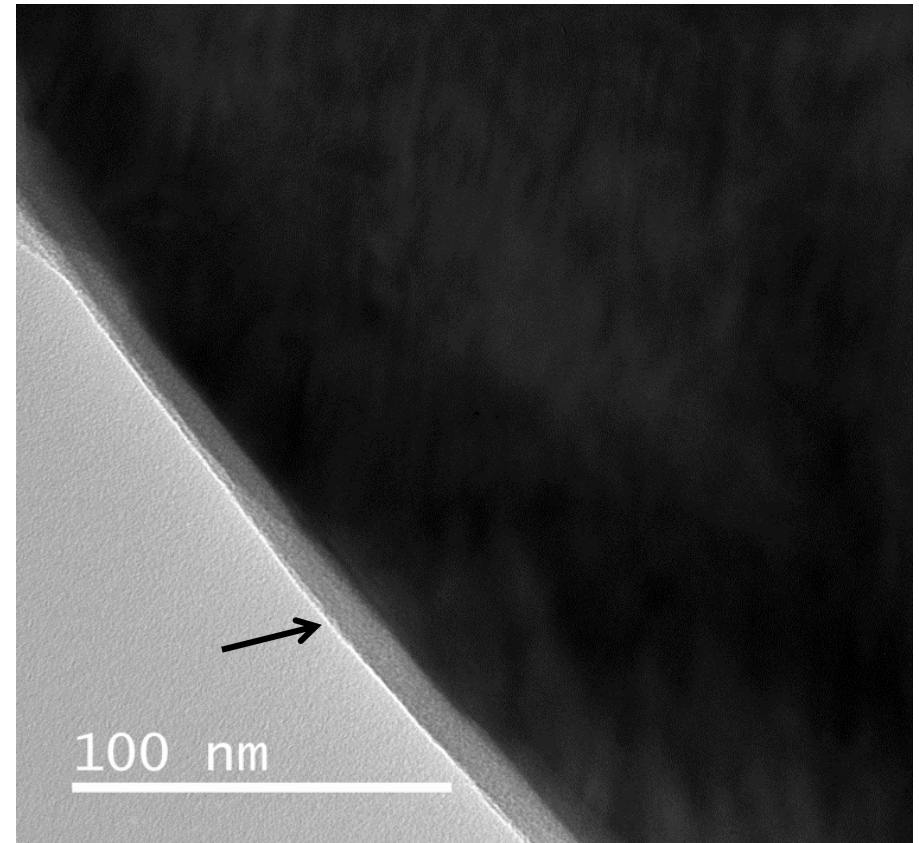


Defects in **raw** KNN SPS sintered



disturbed contrasts
→ stresses
→ crystallites' defects

a



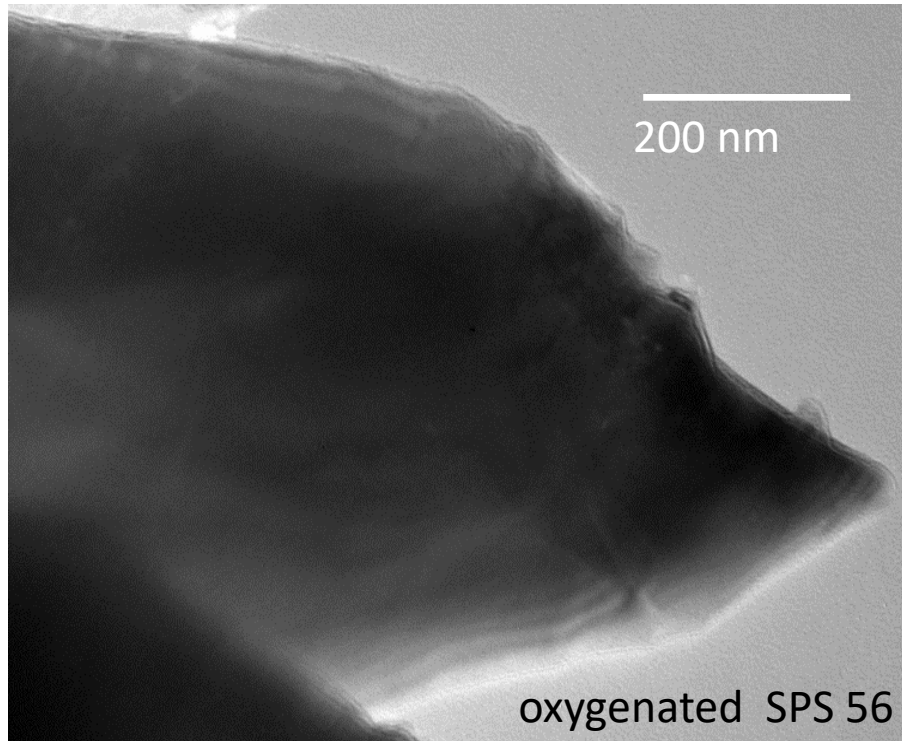
Systematically,
amorphous carbon strips (few nm)
around the grains.

b

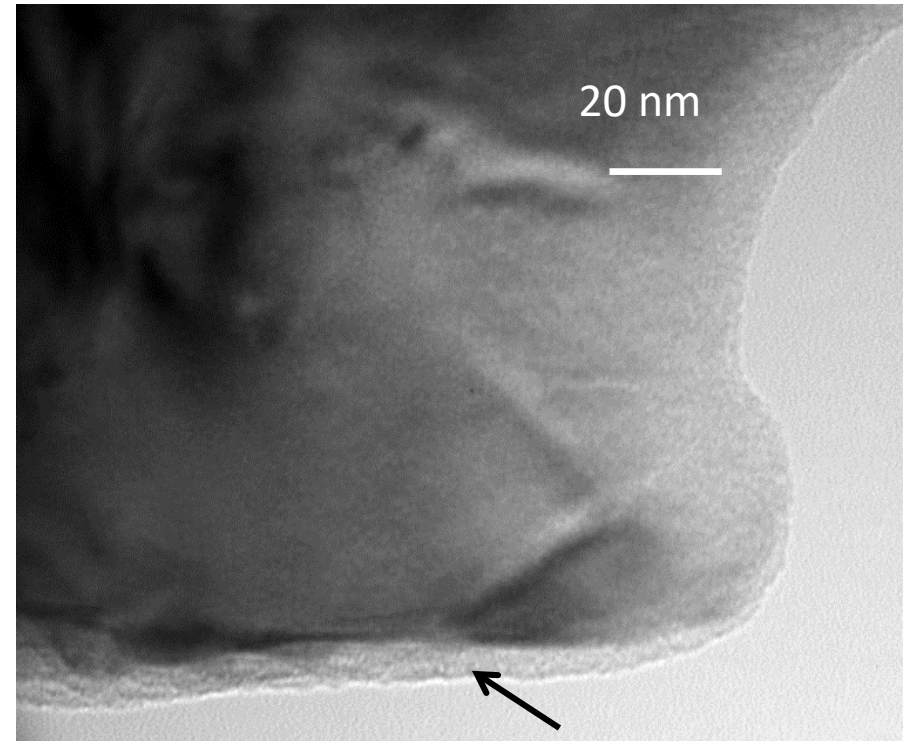




After oxygen annealing



a



b

Regular and homogeneous
contrasts → low stress
→ Low defects.

No more C on grains' edge

OXYGEN ANNEALING supresses C contamination, stresses and defects





raw SPS-KNN : Electrical conduction

Charge carriers

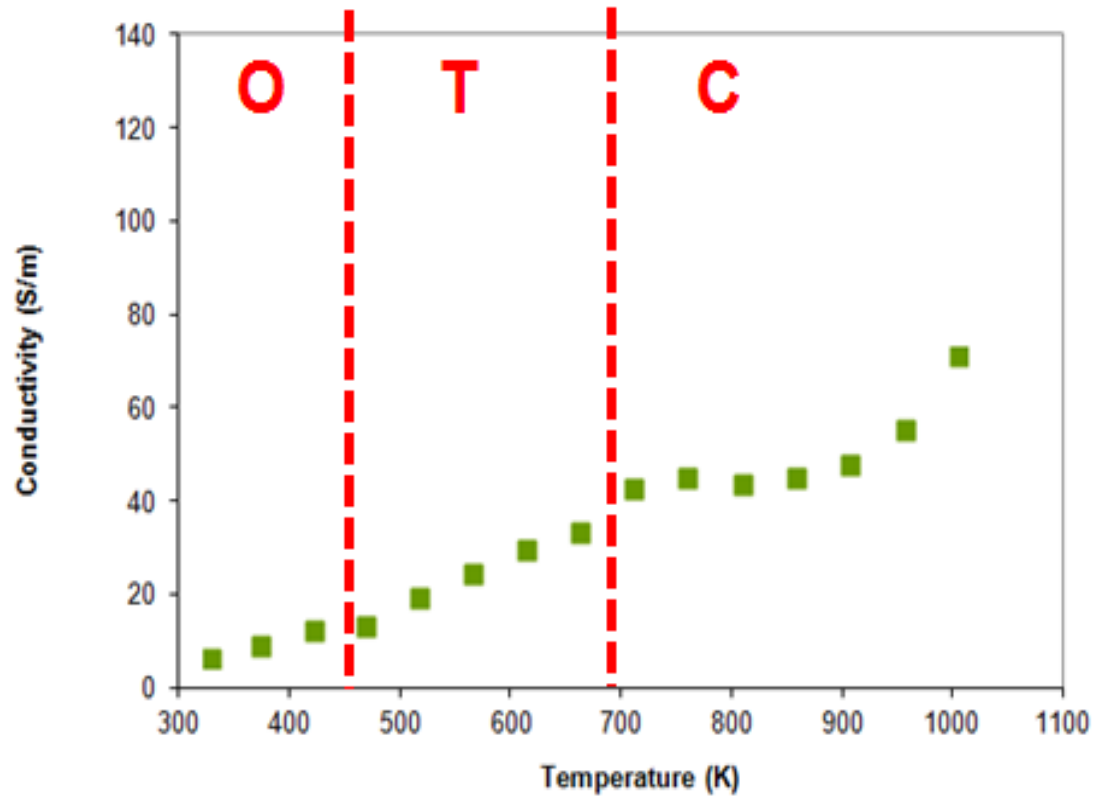


Oxygen vacancies

Oxygen annealing



NO MORE
conductivity



Easy to recover oxygen content

Impact of SPS on thermoelectric oxide :

$$Sr_{0.95}La_{0.05}TiO_3$$


$$ZT = T S^2 \sigma / \kappa = T PF / \kappa$$

S = Seebeck coefficient ($\mu\text{V}/\text{K}$)

σ = Electrical conductivity ($\text{S}\cdot\text{m}^{-1}$)

κ = Thermal conductivity ($\text{W}\cdot\text{m}^{-1}\cdot\text{K}^{-1}$)

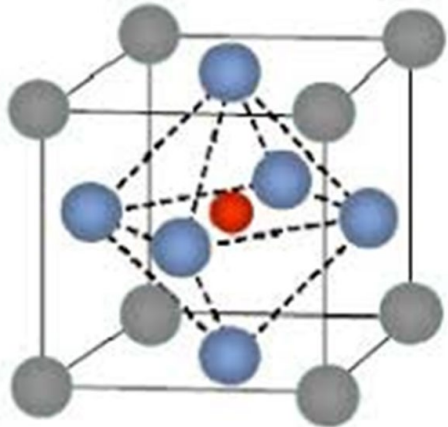
PF = Power factor ($\text{W}\cdot\text{K}^{-2}\cdot\text{m}^{-1}$)



Sr 

Ti 

O 



- Perovskite structure

- N-type Semiconductor with a band gap of 3,2 eV

- **La substitution = High Power factor : $2 \cdot 10^{-3} \text{ W}/\text{m K}^2$**
Okuda et al. Physical Review B 63 (2001) 113104.

- **High thermal conductivity : $7 - 4 \text{ W}/\text{m K}$**

Muta et al. Journal of alloys and compounds 350 (2003) 292?



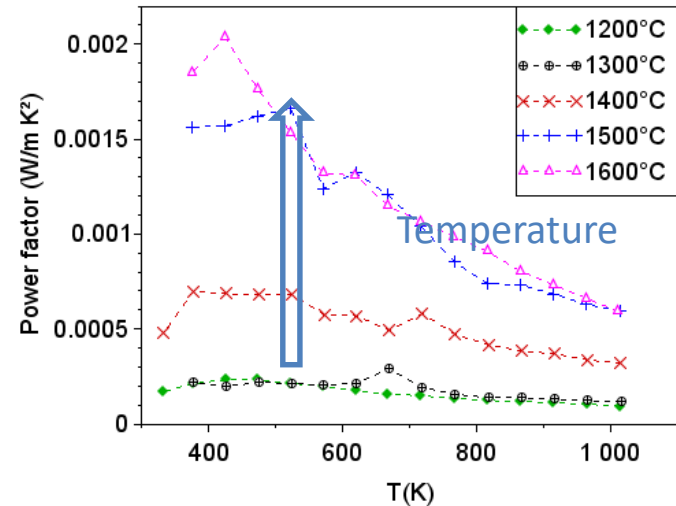
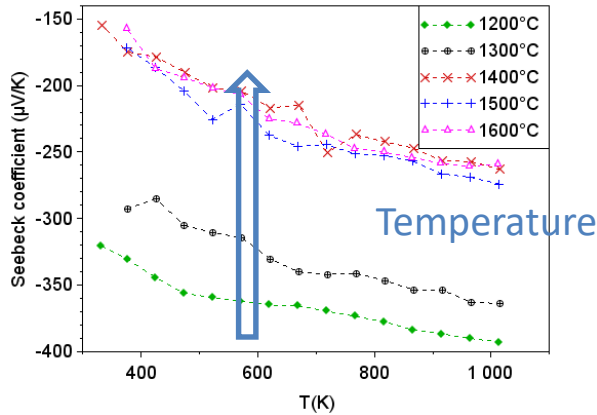
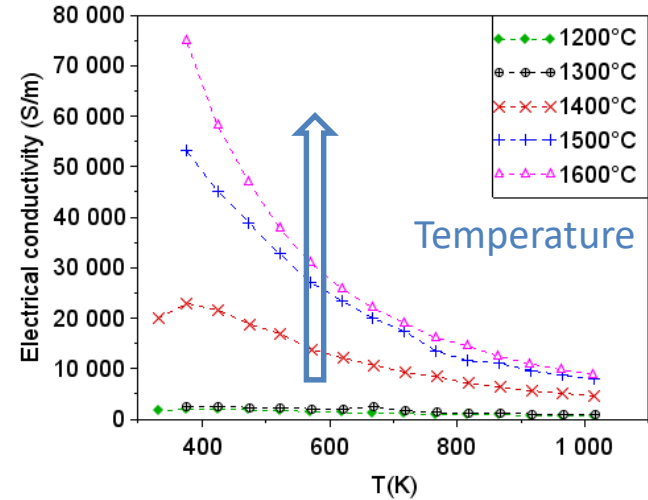
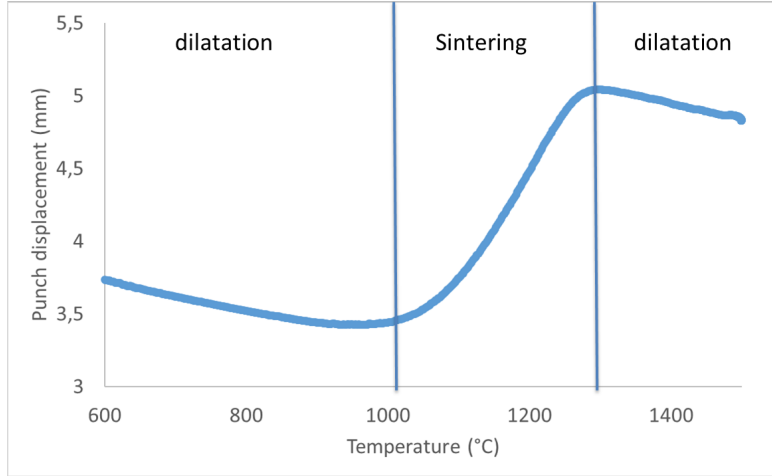
Optimized properties require sintering under Ar/H_2 or long term annealing at 1400°C under Ar/H_2 after sintering



SPS

SPS Conditions

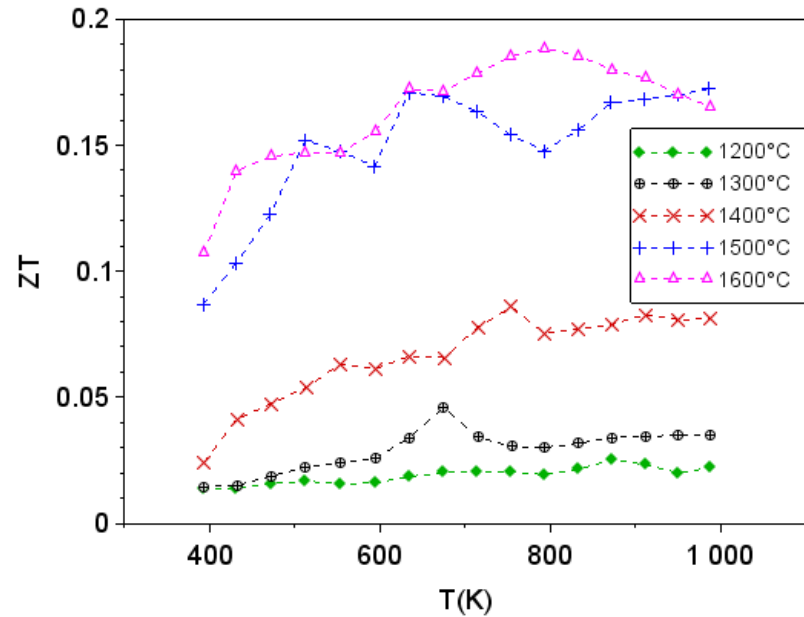
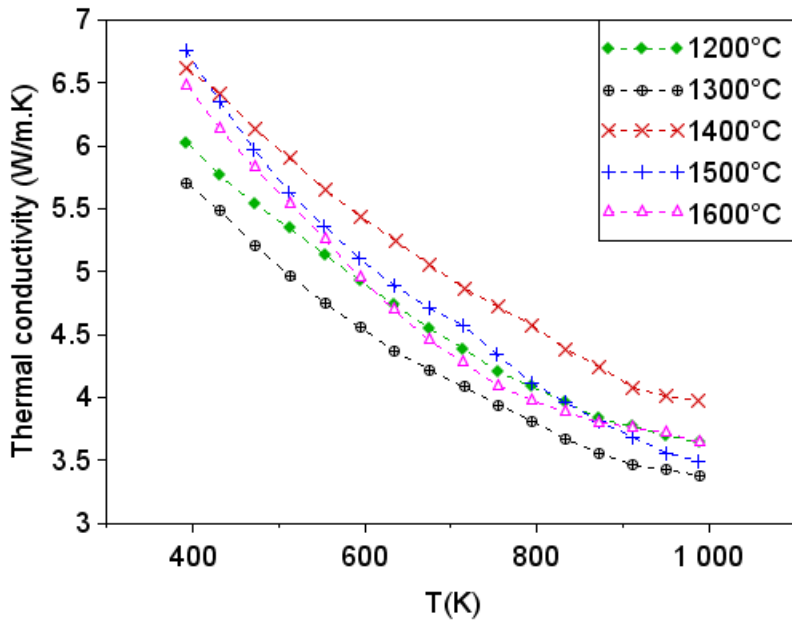
80 MPa
10 min



with increasing sintering temperature

- Electrical conductivity increases
- Seebeck coefficient value decreases with sintering temperature
- PF of 2 mW/m K² is reached at 100°C with a sintering temperature of 1600°C



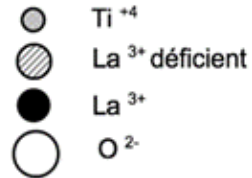
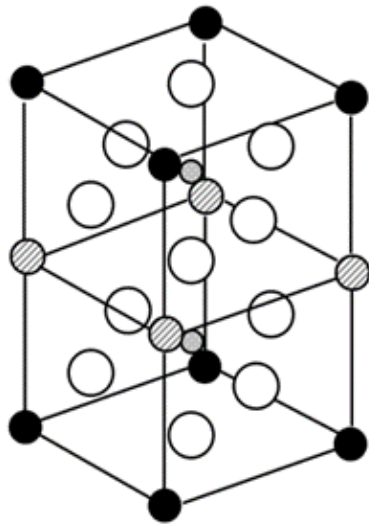


- Thermal conductivity evolution does not shown clear trend
- ZT reaches 0.15 @ 400K and 0.19 @ 800K
- No more post annealing under Ar/H₂
- Fast process (few minutes versus several hours)



Impact of SPS on thermoelectric oxide :





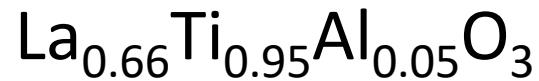
A-deficient perovskite

c parameter doubling

Stabilization with Al



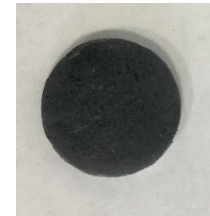
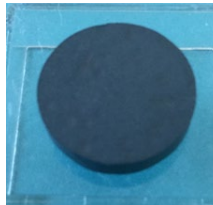
Abe et al (1974) Mat. Res. Bull. 1974

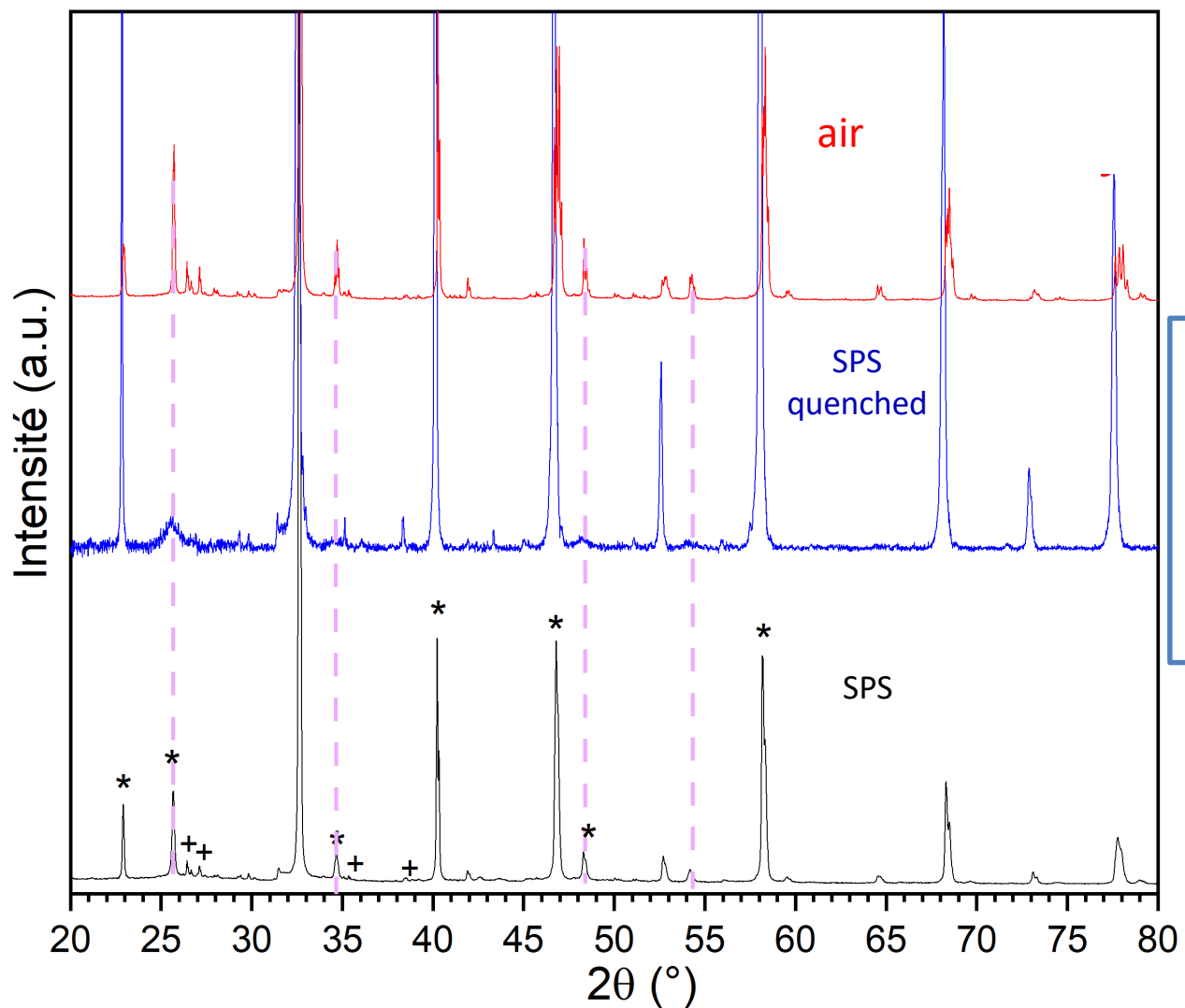
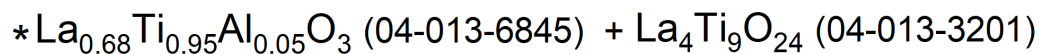


Thermal conductivity decreases



	air	air + annealing	Ar/H2	SPS	SPS quenched
Sintering temperature	1400°C	1400°C	1400°C	1300°C	1300°C
Time	8 h	8 h	8 h	5 min	0
Time and temperature of Ar/H ₂ annealing		76 h 1300°C			
Density	90%	90 %	92 %	98%	98%





- Expected phase
- Impurities
- Quenched = low intensity of surstructure peaks

Rietveld fit of SPS Quenched

$Pmmm$

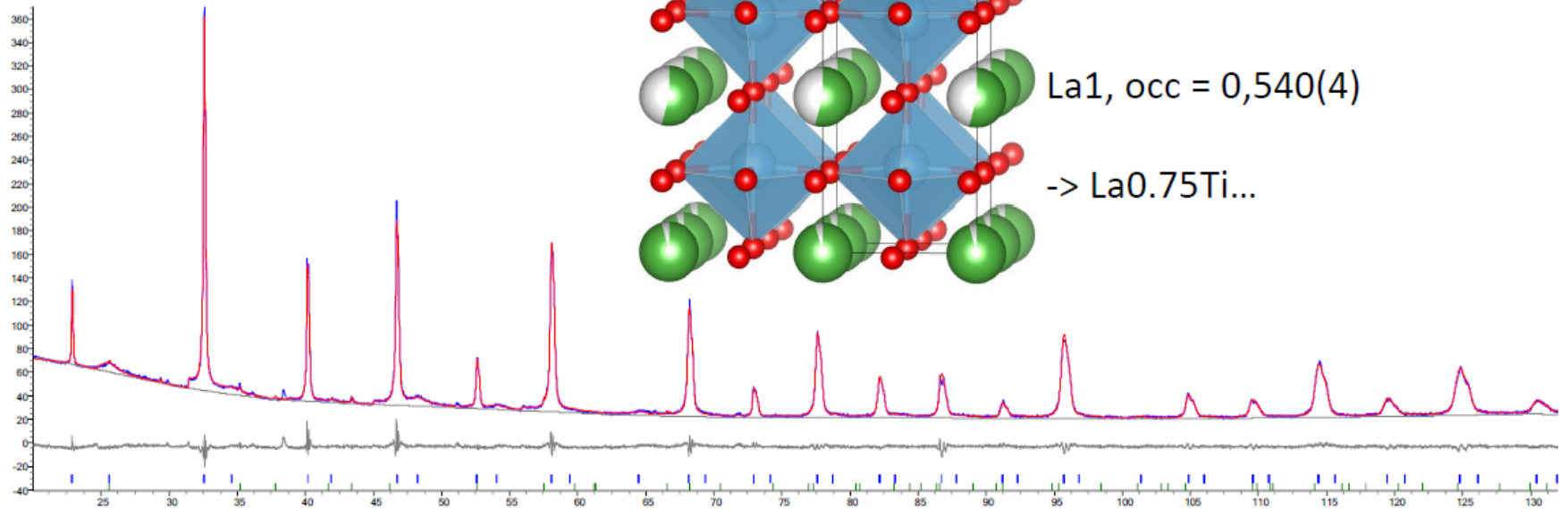
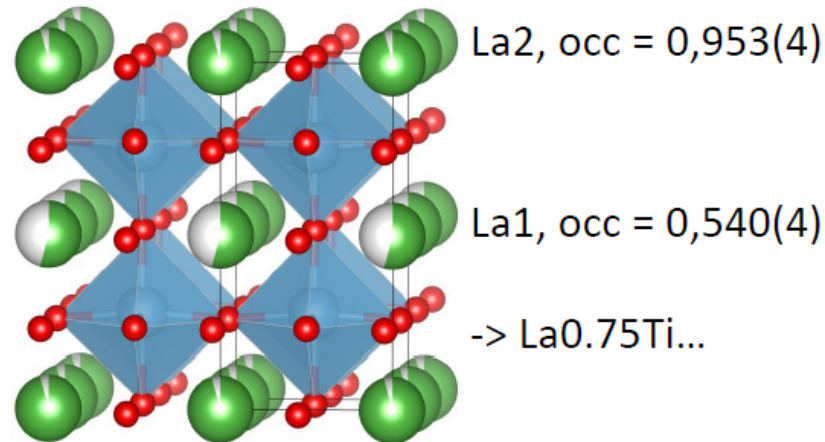
$a = 3,888(2) \text{ \AA}$

$b = 3,888(2) \text{ \AA}$

$c = 7,778(2) \text{ \AA}$

La, Ti parameters refined freely

O parameters fixed to published values

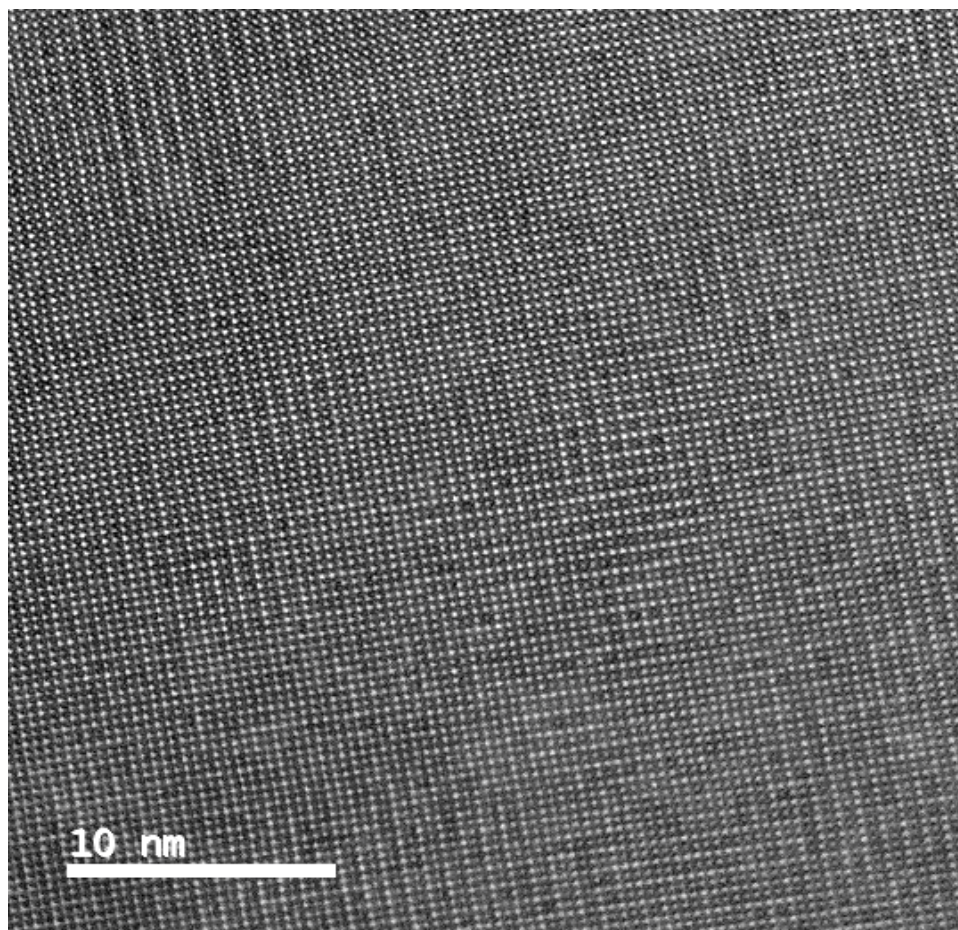


$Pmmm$ is still good enough to produce a good Rietveld fit with reliable refined occupancies

→ The sample is fully-ordered at the unit-cell level

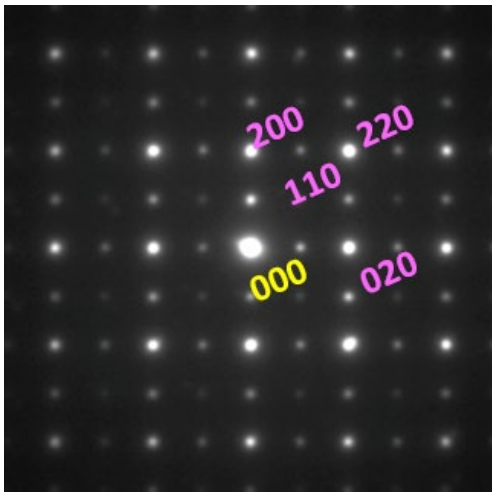
→ The ordered domains have a size distribution centred around 6 nm



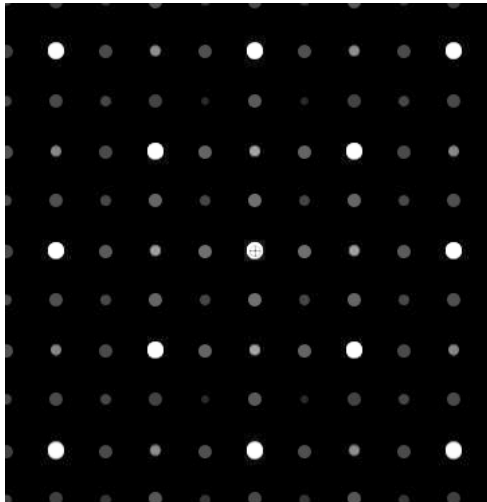
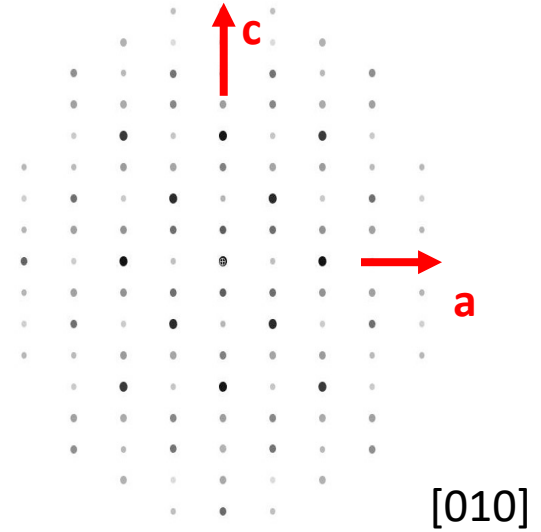
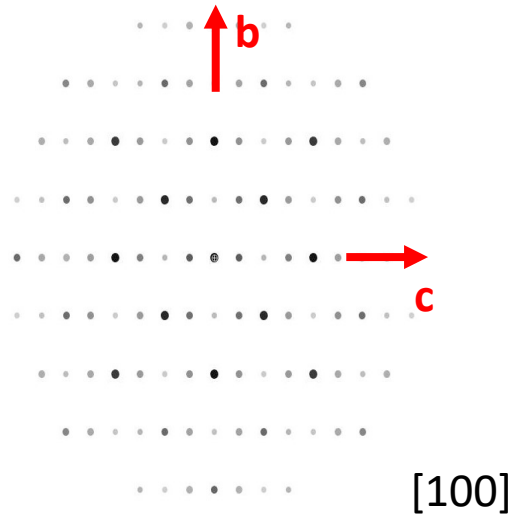


STEM-HAADF image at the atomic resolution of the quenched sample prepared as a thin lamella.

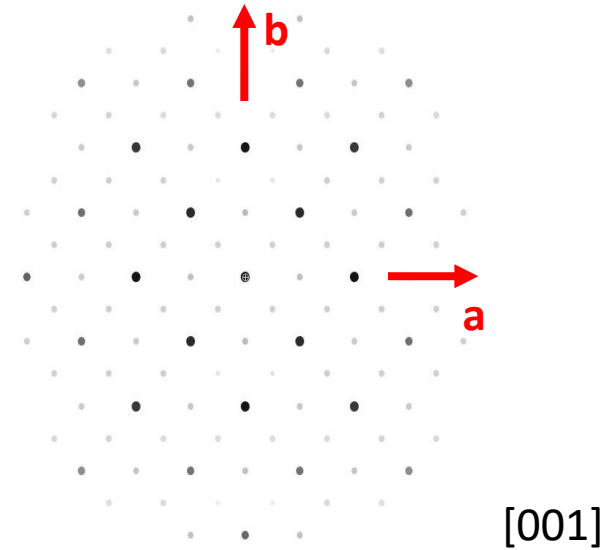


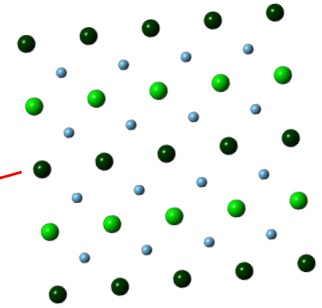
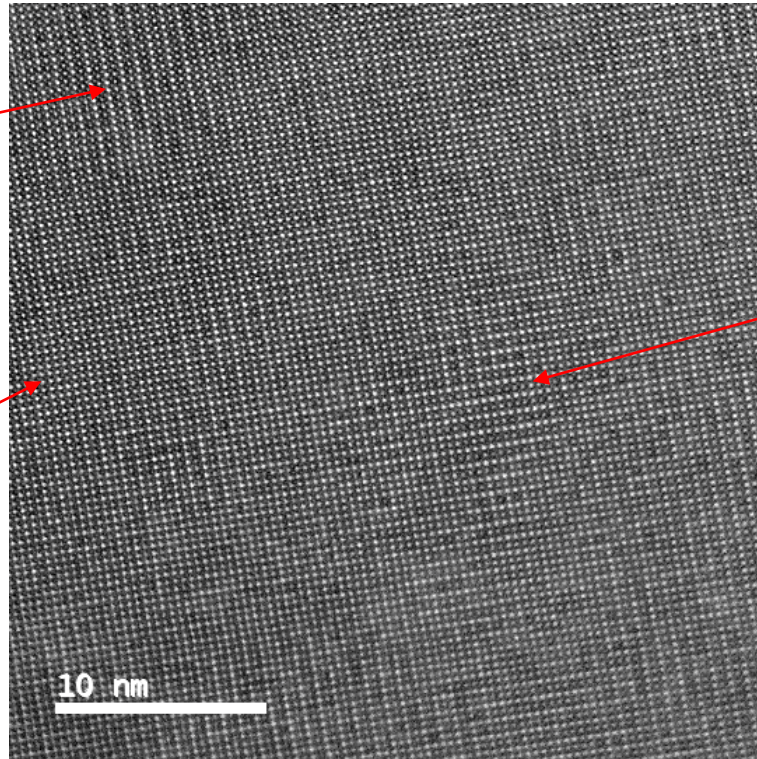
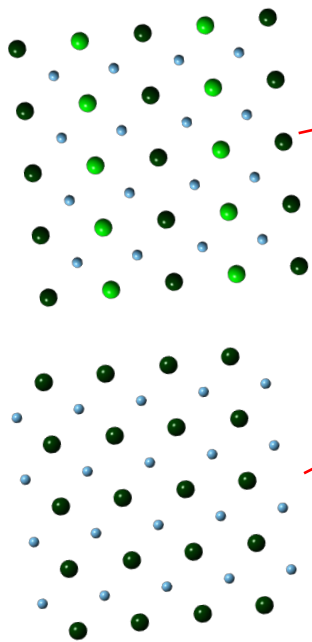


Selected Area Electron Diffraction pattern obtained, along the [100] zone axis family ([100], [010], [001]).



By superposition of the 3 simulated electron diffraction patterns we can reproduce an electron diffraction pattern with a very good match with the experimental SAED.



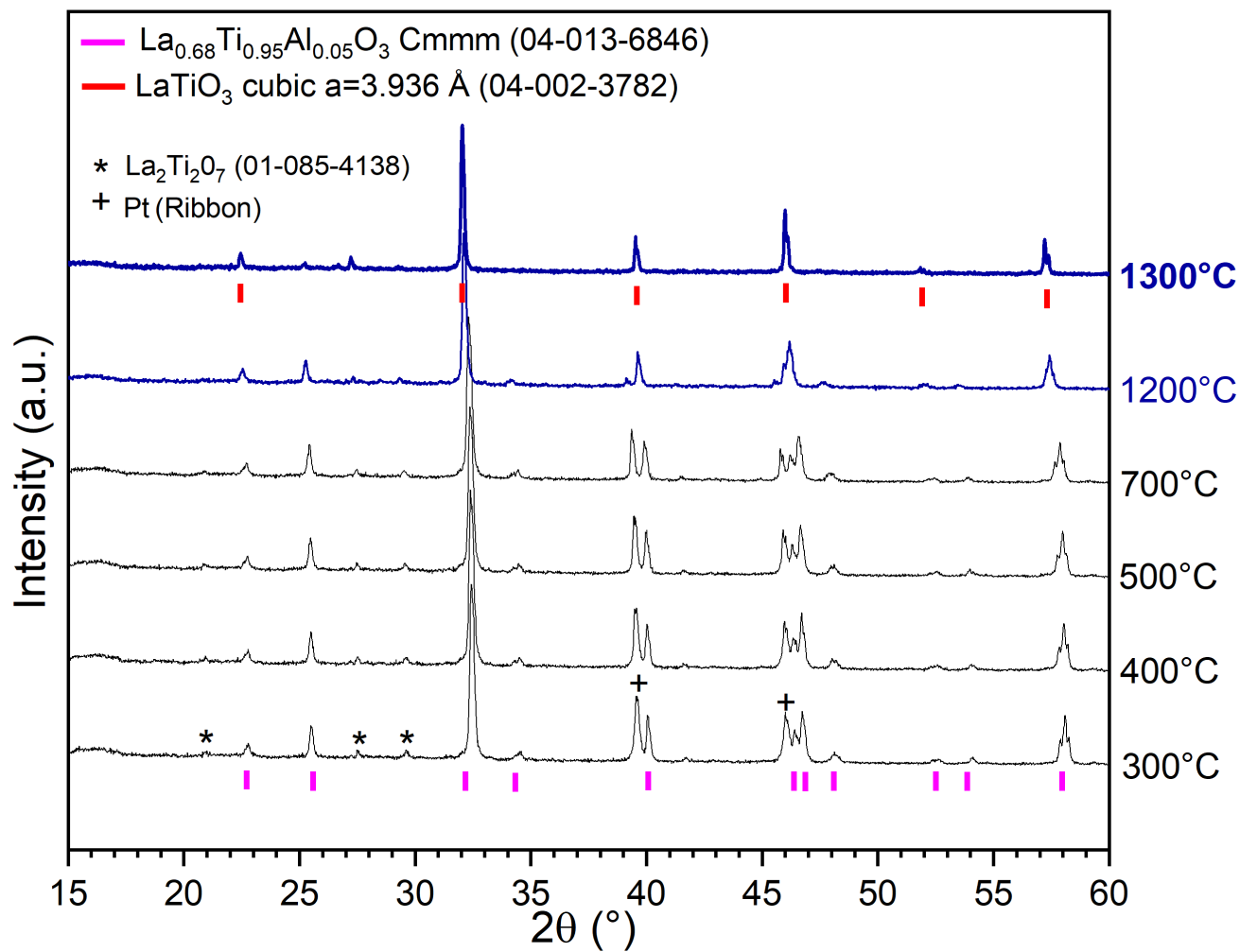


STEM-HAADF image at the atomic resolution of the quenched sample.

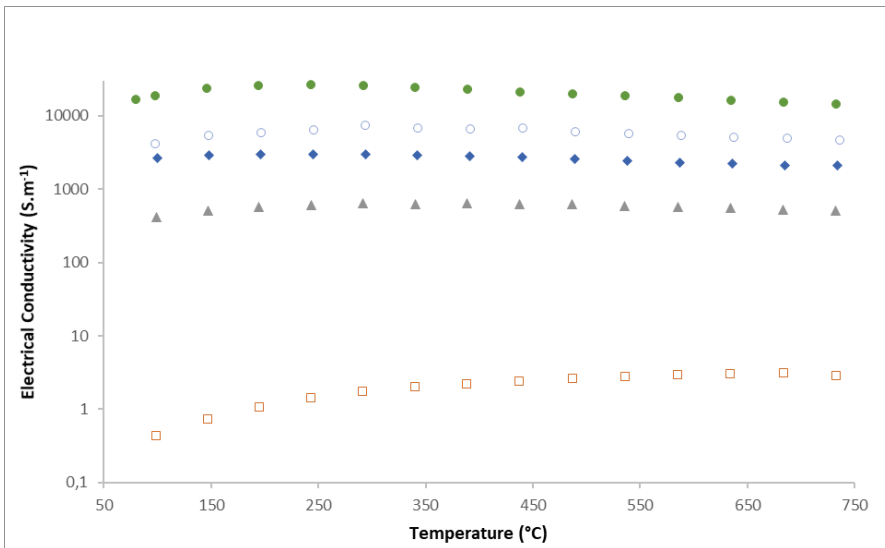


Presence of nanodomains





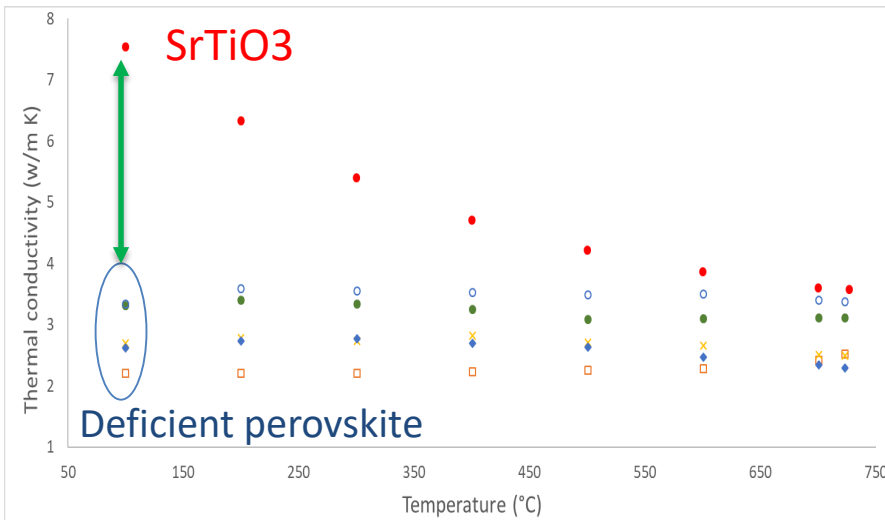
High temperature cubic phase



SPS-quenched
SPS
Sintering Ar/H₂
Annealing Ar/H₂

air

Best PF is obtained for the quenched sample



The thermal conductivity is divided by 2 at 100°C in comparison of SrTiO₃

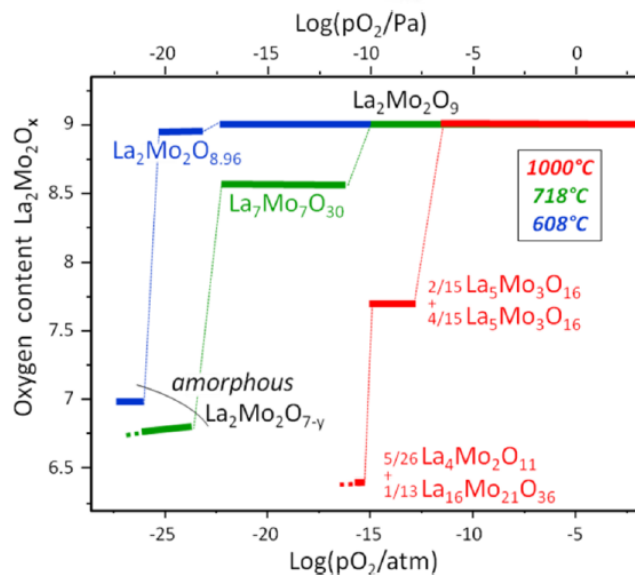
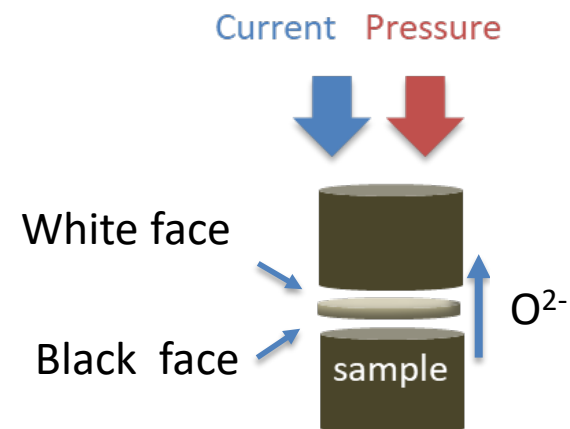
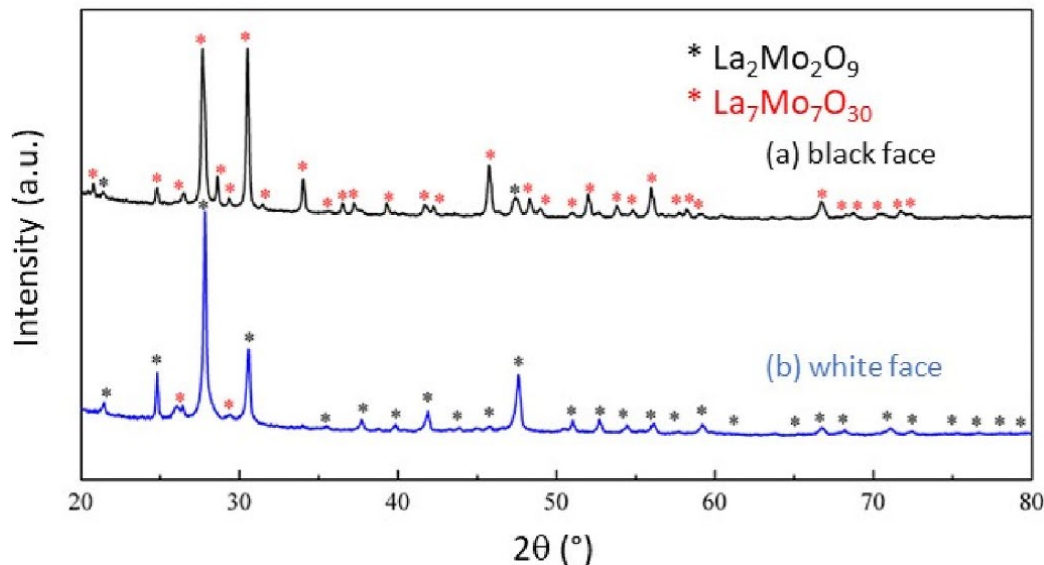
ZT of 0.12 is reached at 1000K



Impact of SPS on Ionic conductor : $\text{La}_2\text{Mo}_2\text{O}_9$



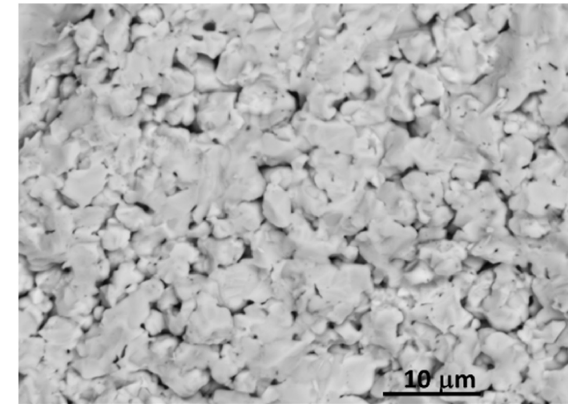
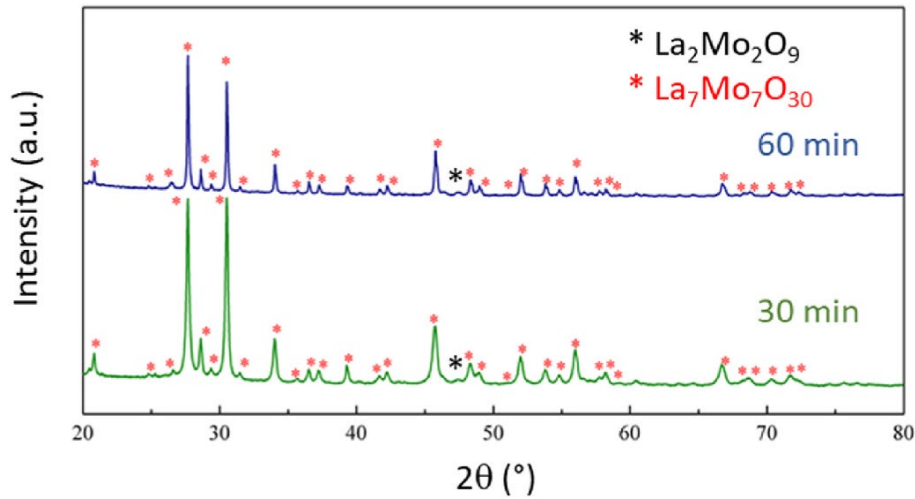
SPS 700°C , 5 min, 90 MPa



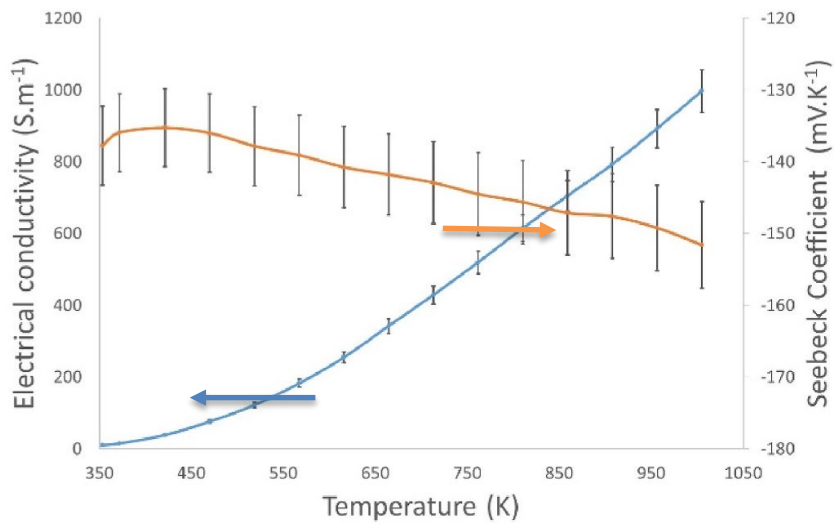
$\text{La}_2\text{Mo}_2\text{O}_9$ in situ transformation in reduced phase $\text{La}_7\text{Mo}_7\text{O}_{30}$

Buvat et al. Inorg. Chem. 55 (2016) 2522

SPS 700°C , 90 MPa



89 % relative density



Thermoelectric properties evaluation of
the reduced phase $\text{La}_7\text{Mo}_7\text{O}_{30}$
 $ZT = 0,04$ @ 1000K

Conclusion

- Oxygen annealing allows recovering piezoelectric material in KNN
- Reducing atmosphere leads to good thermoelectric properties without Ar/H₂ annealing
- Quenched La_{0,66}Ti_{0,95}Al_{0,05}O₃ sample exhibits nanodomains
- In situ transformation of La₂Mo₂O₉
- Obtention of La₇Mo₇O₃₀ ceramic

SPS could be advantage or disadvantage depending on what we are looking for but obviously new opportunities